NSN 5962-01-040-7663

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View Online at https://aerobasegroup.com/nsn/5962-01-040-7663

Body Length:

Between 0.740 inches and 0.810 inches

Body Width:

Between 0.280 inches and 0.310 inches

Body Height:

Between 0.110 inches and 0.140 inches

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Receiving set, countermeasures type an/wlr- (v) 2

Features Provided:

Hermetically sealed and monolithic and bipolar and w/buffered output and w/decoded output and w/enable and w/disable and w/storage and

positive outputs and programmable and programmed

Inclosure Material:

Ceramic and glass

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

10 input

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

5.5 volts power source

Time Rating Per Chacteristic:

125.00 nanoseconds propagation delay time, low to high level output and 65.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Rom

Memory Capacity:

Unknown

Test Data Document:

07397-15-808654 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing,

etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

16 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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- Demilitarization:

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